

Table of Contents

Preface

Intrinsic/Internal Gettering in Czochralski Silicon Wafers F. Shimura	1
Defects and impurities in Multi Layer Structures on Si: The Role of Mechanical Stresses in Gettering of Defects and Impurities by Intrinsic and Extrinsic Grain Boundaries	13
Precipitation of Iron in Silicon: Gettering to Extended Surface Defects Sites M.D. de Coteau, P.R. Wilshaw and R.J. Falster	27
Gettering of Copper and Nickel in Czochralski Silicon by Oxide Particles: Assessment of Thermal Stability R.J. Falster, Z. Laczik, G.R. Booker and P. Török	33
Gettering of Copper and Nickel in Czochralski Silicon by Oxide Particles: Dependence on Oxide Particle Density and Cooling Rate Z. Laczik, R.J. Falster and G.R. Booker	39
On the Role of Stacking Faults in Copper Precipitation in Silicon M. Seibt	45
TEM Studies of the Gettering of Copper, Palladium and Nickel in Czochralski Silicon by Small Oxide Particles A.R. Bhatti, R.J. Falster and G.R. Booker	51
An Influence of Carbon on Intrinsic Gettering Quality and Circuit Performance L. Tesar, J. Fojtášek, J. Kadanka and J. Bartoš	57
Intrinsic Gettering in Nitrogen-Doped Cz-Si J.S. Yang, L.B. Li and D.L. Que	65
Application of Doped Polysilicon Layers in a BICMOS-Technology G. Ritter, H.B. Erzgräber and D. Bolze	69
Self-Interstitial Atoms and Structure of Intrinsic Getter in Silicon Crystals L.I. Fedina, S.G. Denisenko and A.L. Aseev	79
Internal Gettering Effectiveness for Transition Metals /Fe,Ni/ in Cz-Si U. Wojciechowski	85
Intrinsic Gettering of Radiation Defects in Silicon Caused by High-Temperature Oxygen-Containing Defects V.B. Neimash, T.R. Sagan, V.M. Tsmots, V.M. Siratskii, V.I. Shakhovtsov and V.L. Shindich	87
Defect Engineering in Submicron CMOS Technologies C. Claeys, J. Vanhellemont and E. Simoen	95
Contamination Control in Si ULSI-Technology at the 10^{11}cm^{-3} - Level and below W. Bergholz, G. Zoth, G. Götz and A. Saliov	109
Point Defect Engineering for ULSI Silicide Processing G.A. Rozgonyi and J.W. Honeycutt	121
Defect Control and Gettering in Cz-Silicon F.G. Kirscht, E.R. Weber and I. Babanskaya	137
Silicon Device Engineering by Intrinsic Point Defect Control N.A. Sobolev, Y.V. Vyzhigin, B.N. Gresserov, E.I. Sheck, A.I. Kurbakov, E.E. Rubinova and V.A. Trunov	169
Defect Engineering in a High-Voltage Substrate Technology G. Kissinger, W. Kissinger, K. Tittelbach-Helmrich, U. Retzlaff, J. Knopke, K. Schmalz and G. Morgenstern	175
Thermal Wafer Warpage and its Avoidance A. Fischer and H. Richter	181
Defects in Crystalline Silicon - History and Outlook E. Sirtl	189
Defect Spectroscopy in Compound Semiconductors H.G. Grimmeiss and M. Kleverman	195
Formation and Defect Structure of FeIn Pairs in Silicon W. Gehlhoff, P. Emanuelsson, P. Omeling and H.G. Grimmeiss	207

EPR Identification of Mn- or Cr-Acceptor Pairs in Silicon J. Kreissl, W. Gehlhoff, K. Irmscher, P. Omling and P. Emanuelsson	215
The Influence of RTA on Deep States in Si-Implanted GaAs MESFET Structures Investigated by DLTS and ODLTS F. Dubecky and T. Lalinsky	221
Study of Electron and Hole Emission from Deep States in Undoped Semi-Insulating GaAs by PICTS and Photo-DLTS F. Dubecky, G. Papaioannou, V. Ioannou-Sougleridis and M. Baumgärtner	227
'New Donors' in Heat-Treated Cz-Si - What is Really New There? V.V. Emtsev, Y.N. Daluda and K. Schmalz	229
The Thermal Acceptor in Nitrogen Doped Cz Silicon D.S. Yang, J. Lu, L. Li, H. Yao and D.L. Que	235
On Carbon-Implantation Induced Donors in Silicon K. Schmalz, P. Gaworzewski, R. Winkler and W. Skorupa	241
A Search on the Identity of the $E_v+0.34$ eV C-Related Defect in p-Si C.A. Londos	247
Simulation of Hydrogen Diffusion in n and p Type Silicon: Determination of Kinetic and Thermodynamic Parameters D. Ballutaud, R. Rizk and P. de Mierry	253
Hydrogen Passivation of Grain Boundaries in Polysilicon: Computer Simulation L.E. Polyak and E.A. Katz	259
Modification of the Properties of Si Crystals Exposed to Atomic Hydrogen at High Temperatures S.V. Koveshnikov, S.V. Nosenko and A.M. Surma	265
Simulation of Point-Defect Assisted Diffusion of Boron in RTA-Treated Silicon Wafers H. Gdanitz and G. Ritter	271
Dopant Deactivation and Electrically Active Defects Induced in Silicon by CF_4 and $CBrF_3$ Plasma Etching Y.P. Baryshev, A.A. Orlikovsky, K.A. Valiev and M.N. Zolotukhin	277
Formation and Properties of Metastable Silicide Precipitates in Silicon M. Seibt and W. Schröter	283
Mechanical Behaviour of Semiconductors in Terms of Dislocation Dynamics I. Yonenaga and K. Sumino	295
Dislocation Kink Dynamics and Gettering Processes in Semiconductors B.Y. Farber, Y.L. Iunin, V.I. Nikitenko and V.I. Orlov	311
Local Distribution of Structure Defects Induced by Microhardness Indentation in GaAs T. Wosiński, O. Breitenstein, C. Eisenschmidt and L. Fang	323
Dynamics of a Dislocation in the Potential Relief of Semiconductor Crystals under Varying Applied Forces D.A. Kamaev and V.M. Chernov	329
Peculiarities of Dislocation Luminescence of Covalent Semiconductors A.N. Izotov, A.I. Kolyubakin, S.A. Shevchenko and E.A. Steinman	335
Defects in Multicrystalline Silicon R. Schindler and A. Räuber	341
Origin of Recombination at Extended Defects: EBIC Contrast Experiments and Theory on Dislocations in GaAs B. Sieber	353
Electrical Properties of Dislocation Impurity Atmospheres in Si E.B. Yakimov, N. Yarykin and S.V. Koveshnikov	367
Electrical Properties of Defects in Multicrystalline Silicon M. Kittler, J. Lärz, G. Morgenstern and W. Seifert	373
Process Induced Defects in $TiSi_2-N^+/P$-Structures H.B. Erzgräber, P. Zaumseil, E. Bugiel, R. Sorge, K. Tittelbach-Helmrich and F. Richter	379
Evolution of Process - Induced Defects in Silicon under Hydrostatic Pressure A. Misiuk	387
Evolution of Monoclinic SiAs Precipitates in Heavily As^+ Implanted and Isothermally Annealed Silicon A. Armigliato, A. Parisini, M. Derdour, P. Lazzari, L. Moro, D. Nobili and S. Solmi	393

Defect Structures in Si Preamorphized Wafers S. Prussin	399
Behavior of Implanted Nitrogen in Si with the Buried Layer of SiO₂ Precipitates A.B. Danilin, K.A. Drakin, A.A. Malinin, V.N. Mordkovich, A.F. Petrov and O.I. Vyletalina	405
Interaction of Implanted into Silicon Fluorine with Radiation Defects L.Y. Krasnobaev, A.A. Malinin, V.V. Makarov and I.B. Sayapin	411
Electrical Activity of Halogen-Silicon Complexes L.Y. Krasnobaev and N.M. Omelyanovskaya	417
Radiation Defect-Induced Optical Absorption of GaP C. Ascheron, H. Neumann, W. Hörig and G. Nooke	423
Synchrotron Radiation X-Ray Topography of Growth Striations in Magnetic-Field-Applied Czochralski Silicon S. Kawado, S. Kojima, I. Maekawa and T. Ishikawa	429
Applications of In Situ Transmission Electron Microscopy to the Characterization of Process-Induced Defects M. Reiche and J. Heydenreich	439
TEM Techniques for 2D Junction Delineation and Correlation with SIMS and SRP A. Romano-Rodríguez, J. Vanhellemont, A. De Keersgieter, W. Vandervorst and J.R. Morante	449
Defect Generation in Cz-Silicon Used for the Design of Synchrotron Monochromator Crystals P. Zaumseil, U. Winter and S. Joksche	455
X-Ray Diffractometry and Topography of CdHgTe Bulk Crystals and CdHgTe-CdTe Epitaxial Structures V.V. Ratnikov, T.S. Argunova, K.E. Mironov and L.M. Sorokin	461
Grazing Incidence Diffraction X-Ray Topography R.M. Imamov and D.V. Novikov	467
Indirect Excitations in the X-Ray Standing Wave Method A.V. Maslov	471
Double-Channel X-Ray Standing Wave Technique for Impurity Atom Location in Multicomponent Crystals E.K. Mukhamedzhanov	475
Spectroscopical and Electrical Evidences about Segregation Effects in Semiconductors S. Pizzini, M. Acciarri and S. Binetti	479
DLTS of High-Resistivity Si E. Simoen, C. Claeys, G. Huylebroeck and P. Clauws	493
Evaluation of DLTS Measurements in the Case of "Broadened" Spectra or a Barrier Limited Capture Process K. Tittelbach-Helmrich	499
B-Ion Implantation into Mo-Film for Shallow Junction Formation: DLTS Analyses on the p⁺/n Fabricated Diodes A. Poggi, R. Angelucci, E. Susi and M. Merli	505
Electrical Evaluation of Silicon on Insulator Structures Formed by Oxygen Implantation by Means of Frequency Resolved Photoconductivity Measurements F. Coromina, A. Pérez-Rodríguez, J.R. Morante, M.A. Lourenço, K.P. Homewood and P.L.F. Hemment	511
Nonlinear Recombination and Diffusion Processes in Si and GaAs D. Noreika, V. Netiksis, M. Petrauskas and M. Lenzner	517
Carrier Recombination Processes in PbTe Films by Picosecond IR Excitation R. Tomasiusas, R. Masteika, K. Tumkevicius and M. Petrauskas	523
Investigation on Electrical Contacts on N-Type Silicon A. Castaldini, D. Cavalcoli and A. Cavallini	529
Diagnostics of Defects from the Noise Spectra V.M. Aroutyunyan, F.V. Gasparyan and S.V. Melkonyan	535
Statistical Analysis of the Assembly-Induced Degradation of the Silicon Device Parameters F. Gaiseanu	541
Mechanical Strain Relaxation during Lattice-Mismatched Epitaxial Growth A. Schlachetzki and H.-. Wehmann	551

Interfacial Dislocations in the GaSb/GaAs (001) Heterostructure A.M. Rocher	563
Si/Ge - Heterostructures - Stability of Strained Layer Superlattices E. Kasper	573
Distribution of Defects in $\text{InAs}_{1-x-y}\text{Sb}_x\text{P}_y$-InAs DHs T.S. Argunova, R.N. Kyutt, B.A. Matveev, S.S. Ruvimov, N.M. Stus' and G.N. Talalakin	581
Nature of Defects in MOCVD Grown GaAlAs-GaAs QW DHs B.S. Yavich, I.N. Kochnev, P.P. Buinov, N.I. Katzavetz, T.S. Argunova, G.N. Mosina and S.S. Ruvimov	587
XPS Sputter Depth Profiling Applid to the Analysis of Si/SiO₂, Si/SiO_xN_y and Si/Si₃N₄ O. Benkherourou and J.P. Deville	593
Electrical Stability of Thin Nitroxide Layers on Silicon after RTO/RTN/RTO-Treatment G. Weidner, G. Prösch, A. Beyer, M. Wolf, V. Rank and M. Kopp	599
Germanium and Antimony Epitaxy with Large Lattice Misfit H.J. Osten, J. Klatt and G. Lippert	605
TEM Investigations on the Structure and Stability of Diffusion Barriers for VLSI Contacts S. Hopfe and M. Reiche	611
Defect Characterization of Thick SOI-Layers and Eptaxial Grown Layers on SOI Substrates K. Höppner, B. Tillack, R. Banisch, H.H. Richter and O. Joachim	617
SOI by Silicon Wafer Direct Bonding - Problems of Wafer Warpage and Surface Chemistry G. Kissinger, W. Kissinger, H. Hofmann and J. Krüger	625
Temperature Profiles Induced by Recrystallization of Silicon-on-Insulator with Scanning Incoherent Light Line Source H.H. Richter, H. Andrä, B. Tillack, O. Joachim, W. Weinelt, R. Banisch and K. Hoeppner	631
Zinc and Zinc-Impurity Pairs in Silicon C.A.J. Ammerlaan and H.E. Altink	639